

CLEANING AGENT FOR SEMICONDUCTOR PROVIDED WITH METAL WIRING

ABSTRACT

A cleaning agent for a microelectronic device provided with metal wiring, which has an excellent ability to remove polishing particle residues derived from a polishing agent and an excellent ability to remove metallic residues on an insulating film, and has excellent anticorrosiveness to the metal wiring. The cleaning agent is used at a step subsequent to chemical mechanical polishing in a manufacturing process of a microelectronic device in which a metal wiring, e.g., copper or tungsten, is formed.